

Notice of References Cited

Application/Control No.

09/887,199

Applicant(s)/Patent Under
Reexamination
RAAIJMAKERS ET AL.

Examiner

Anh D. Mai

Art Unit

2814

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U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-Pub-2002/0031618	03-2002	Sherman	427/569
	B	US-6203613	03-2001	Gates et al.	117/104
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	J.M. Hergenrother et al., 50 nm Vertical Replacement-Gate (VRG) nMOSFETs with ALD HfO ₂ and Al ₂ O ₃ Gate Dielectrics. IEDM 2001, pp. 51-54.
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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